

# Karen L Kavanagh

## List of Publications by Citations

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192  
papers

6,751  
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38  
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79  
g-index

205  
ext. papers

7,210  
ext. citations

4.1  
avg, IF

5.44  
L-index

#	Paper	IF	Citations
192	Surface plasmon sensor based on the enhanced light transmission through arrays of nanoholes in gold films. <i>Langmuir</i> , <b>2004</b> , 20, 4813-5	4	620
191	Generation of misfit dislocations in semiconductors. <i>Journal of Applied Physics</i> , <b>1987</b> , 62, 4413-4420	2.5	440
190	A new generation of sensors based on extraordinary optical transmission. <i>Accounts of Chemical Research</i> , <b>2008</b> , 41, 1049-57	24.3	423
189	Strong polarization in the optical transmission through elliptical nanohole arrays. <i>Physical Review Letters</i> , <b>2004</b> , 92, 037401	7.4	384
188	Nanohole-Enhanced Raman Scattering. <i>Nano Letters</i> , <b>2004</b> , 4, 2015-2018	11.5	382
187	Luminescent colloidal silicon suspensions from porous silicon. <i>Science</i> , <b>1992</b> , 255, 66-8	33.3	206
186	Asymmetries in dislocation densities, surface morphology, and strain of GaInAs/GaAs single heterolayers. <i>Journal of Applied Physics</i> , <b>1988</b> , 64, 4843-4852	2.5	195
185	Nonalloyed ohmic contacts to n-GaAs by solid-phase epitaxy of Ge. <i>Journal of Applied Physics</i> , <b>1987</b> , 62, 942-947	2.5	182
184	Enhanced fluorescence from arrays of nanoholes in a gold film. <i>Journal of the American Chemical Society</i> , <b>2005</b> , 127, 14936-41	16.4	179
183	Thin epitaxial GeBi(111) films: Study and control of morphology. <i>Surface Science</i> , <b>1987</b> , 191, 305-328	1.8	154
182	Fermi-Level Pinning by Misfit Dislocations at GaAs Interfaces. <i>Physical Review Letters</i> , <b>1983</b> , 51, 1783-1786	4	126
181	Resonant optical transmission through hole-arrays in metal films: physics and applications. <i>Laser and Photonics Reviews</i> , <b>2010</b> , 4, 311-335	8.3	124
180	Misfit dislocations in nanowire heterostructures. <i>Semiconductor Science and Technology</i> , <b>2010</b> , 25, 024006	8	122
179	Observation of quantum dot-like behavior of GaInNAs in GaInNAs/GaAs quantum wells. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 2337-2339	3.4	120
178	Growth, branching, and kinking of molecular-beam epitaxial <110> GaAs nanowires. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 3368-3370	3.4	102
177	Lattice compression from conduction electrons in heavily doped Si:As. <i>Physical Review Letters</i> , <b>1988</b> , 61, 1748-1751	7.4	102
176	Effects of GaAs substrate misorientation on strain relaxation in In <sub>x</sub> Ga <sub>1-x</sub> As films and multilayers. <i>Journal of Applied Physics</i> , <b>1998</b> , 83, 5137-5149	2.5	91

175	Heteroepitaxial growth of vertical GaAs nanowires on Si(111) substrates by metal-organic chemical vapor deposition. <i>Nano Letters</i> , <b>2008</b> , 8, 3755-60	11.5	89
174	Apex-Enhanced Raman Spectroscopy Using Double-Hole Arrays in a Gold Film. <i>Journal of Physical Chemistry C</i> , <b>2007</b> , 111, 2347-2350	3.8	87
173	Strain relaxation of compositionally graded In <sub>x</sub> Ga <sub>1-x</sub> As buffer layers for modulation-doped In <sub>0.3</sub> Ga <sub>0.7</sub> As/In <sub>0.29</sub> Al <sub>0.71</sub> As heterostructures. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 1129-1131	3.4	83
172	Structural and Room-Temperature Transport Properties of Zinc Blende and Wurtzite InAs Nanowires. <i>Advanced Functional Materials</i> , <b>2009</b> , 19, 2102-2108	15.6	82
171	Direct measurement of coherency limits for strain relaxation in heteroepitaxial core/shell nanowires. <i>Nano Letters</i> , <b>2013</b> , 13, 1869-76	11.5	69
170	Electron-energy-loss scattering near a single misfit dislocation at the GaAs/GaNAs interface. <i>Physical Review Letters</i> , <b>1986</b> , 57, 2729-2732	7.4	69
169	Enhancement of band edge luminescence in ZnSe nanowires. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 084316	15	67
168	Basis and lattice polarization mechanisms for light transmission through nanohole arrays in a metal film. <i>Nano Letters</i> , <b>2005</b> , 5, 1243-6	11.5	63
167	Effects of rapid thermal annealing on GaInNAs/GaAs multiple quantum wells. <i>Journal of Crystal Growth</i> , <b>1999</b> , 201-202, 419-422	1.6	61
166	Surface plasmon-quantum dot coupling from arrays of nanoholes. <i>Journal of Physical Chemistry B</i> , <b>2006</b> , 110, 8307-13	3.4	56
165	Transport and strain relaxation in wurtzite InAs/GaAs core-shell heterowires. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 152103	3.4	55
164	Silicon diffusion at polycrystalline-Si/GaAs interfaces. <i>Applied Physics Letters</i> , <b>1985</b> , 47, 1208-1210	3.4	55
163	Lattice-strained heterojunction InGaAs/GaAs bipolar structures: Recombination properties and device performance. <i>Journal of Applied Physics</i> , <b>1987</b> , 61, 1234-1236	2.5	51
162	Growth-induced magnetic anisotropy and clustering in vapor-deposited Co-Pt alloy films. <i>Physical Review B</i> , <b>1999</b> , 60, 12826-12836	3.3	49
161	Faster radial strain relaxation in InAs/GaAs core-shell heterowires. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 044301	2.5	48
160	Lattice tilt and dislocations in compositionally step-graded buffer layers for mismatched InGaAs/GaAs heterointerfaces. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1992</b> , 10, 1820		46
159	Probing the electrical transport properties of intrinsic InN nanowires. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 073102	3.4	44
158	Nanometer-resolved spatial variations in the Schottky barrier height of a Au/n-type GaAs diode. <i>Physical Review B</i> , <b>1994</b> , 49, 16474-16479	3.3	43

157	Ohmic contacts to n-GaAs using In/Pd metallization. <i>Applied Physics Letters</i> , <b>1987</b> , 51, 326-327	3.4	43
156	Developing 1D nanostructure arrays for future nanophotonics. <i>Nanoscale Research Letters</i> , <b>2006</b> , 1, 99-109	3.9	42
155	Nanoscale Electrical and Structural Characterization of Gold/Alkyl Monolayer/Silicon Diode Junctions. <i>Journal of Physical Chemistry C</i> , <b>2008</b> , 112, 9081-9088	3.8	37
154	The interdiffusion of Si, P, and In at polysilicon/GaAs interfaces. <i>Journal of Applied Physics</i> , <b>1988</b> , 64, 1845-1854	3.6	36
153	Molecular orientation in octanedithiol and hexadecanethiol monolayers on GaAs and Au measured by infrared spectroscopic ellipsometry. <i>Langmuir</i> , <b>2009</b> , 25, 919-23	4	35
152	Twinning modulation in ZnSe nanowires. <i>Semiconductor Science and Technology</i> , <b>2007</b> , 22, 175-178	1.8	35
151	Geometric limits of coherent III-V core/shell nanowires. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 054301	2.5	34
150	Structure and photoluminescence of ZnSe nanostructures fabricated by vapor phase growth. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 014326	2.5	33
149	Scanning spreading resistance microscopy current transport studies on doped III-V semiconductors. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2002</b> , 20, 1682		33
148	Gas-source molecular beam epitaxial growth and thermal annealing of GaInNAs/GaAs quantum wells. <i>Journal of Crystal Growth</i> , <b>2000</b> , 208, 145-152	1.6	33
147	Relationship between surface morphology and strain relaxation during growth of InGaAs strained layers. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 3744-3746	3.4	32
146	Ballistic electron emission microscopy studies of Au/molecule/n-GaAs diodes. <i>Journal of Physical Chemistry B</i> , <b>2005</b> , 109, 6252-6	3.4	31
145	Field dependent transport properties in InAs nanowire field effect transistors. <i>Nano Letters</i> , <b>2008</b> , 8, 3114-9	11.5	30
144	Defect studies of ZnSe nanowires. <i>Nanotechnology</i> , <b>2008</b> , 19, 215715	3.4	30
143	Correlation of anisotropic strain relaxation with substrate misorientation direction at InGaAs/GaAs(001) interfaces. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 344-346	3.4	30
142	Rectifying characteristics of Te-doped GaAs nanowires. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 182102	3.4	29
141	Calibrated scanning spreading resistance microscopy profiling of carriers in III-V structures. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2001</b> , 19, 1662		29
140	Growth of InAsSb/InAs MQWs on GaSb for mid-IR photodetector applications. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 3563-3567	1.6	27

139	Anisotropic resistivity correlated with atomic ordering in p-type GaAsSb. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 2384-2386	3.4	27
138	Substrate effects on the ferroelectric properties of fine-grained BaTiO <sub>3</sub> films. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 5982-5989	2.5	25
137	Study of $\mu\text{m}$ -scale spatial variations in strain of a compositionally step-graded In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs(001) heterostructure. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 869-871	3.4	25
136	Gas-source molecular beam epitaxial growth, characterization, and light-emitting diode application of In <sub>x</sub> Ga <sub>1-x</sub> P on GaP(100). <i>Applied Physics Letters</i> , <b>1993</b> , 62, 2369-2371	3.4	25
135	Lateral variation in the Schottky barrier height of Au/PtSi/(100)Si diodes. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1994</b> , 12, 2634		25
134	Time dependent ballistic electron emission microscopy studies of a Au/(100)GaAs interface with a native oxide diffusion barrier. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 2965-2967	3.4	24
133	Multiple dislocation loops in linearly graded In <sub>x</sub> Ga <sub>1-x</sub> As (0.53) on GaAs and In <sub>x</sub> Ga <sub>1-x</sub> P (0.32) on GaP. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 500-502	3.4	24
132	Reduction of Gold Penetration through Phenyl-Terminated Alkyl Monolayers on Silicon. <i>Journal of Physical Chemistry C</i> , <b>2012</b> , 116, 17040-17047	3.8	23
131	Preparation of ideal molecular junctions: depositing non-invasive gold contacts on molecularly modified silicon. <i>Nanoscale</i> , <b>2011</b> , 3, 1434-45	7.7	22
130	Improved Performance of Nanohole Surface Plasmon Resonance Sensors by the Integrated Response Method. <i>IEEE Photonics Journal</i> , <b>2011</b> , 3, 441-449	1.8	22
129	Antimony segregation in GaAs-based multiple quantum well structures. <i>Journal of Crystal Growth</i> , <b>2003</b> , 254, 28-34	1.6	22
128	Growth and strain relaxation of GaAs and GaP nanowires with GaSb shells. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 134309	2.5	20
127	Metastable phase formation in the Au-Si system via ultrafast nanocalorimetry. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 093516	2.5	20
126	Aligned Co nanodiscs by electrodeposition on GaAs. <i>Journal of Crystal Growth</i> , <b>2006</b> , 287, 514-517	1.6	20
125	Comparison of strain relaxation in InGaAsN and InGaAs thin films. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 4357-4359	3.4	20
124	Hot-electron attenuation lengths in ultrathin magnetic films. <i>Journal of Applied Physics</i> , <b>2000</b> , 87, 5164-5166	1.6	20
123	Anisotropic structural, electronic, and optical properties of InGaAs grown by molecular beam epitaxy on misoriented substrates. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 1424-1426	3.4	19
122	Lattice strain from substitutional Ga and from holes in heavily doped Si:Ga. <i>Physical Review B</i> , <b>1992</b> , 45, 3323-3331	3.3	19

121	Direct Measurement of the Electrical Abruptness of a Nanowire p-n Junction. <i>Nano Letters</i> , <b>2016</b> , 16, 3982-8	11.5	18
120	Quantum dot-like behavior of GaInNAs in GaInNAs/GaAs quantum wells grown by gas-source molecular-beam epitaxy. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1999</b> , 17, 1649		18
119	Epitaxial BiGaAs diodes via electrodeposition. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2006</b> , 24, 2138		17
118	Epitaxial BiGaAs(111) diodes via electrodeposition. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 022102	3.4	17
117	Planar Ge/Pd and alloyed Au-Ge-Ni ohmic contacts to n-Al <sub>x</sub> Ga <sub>1-x</sub> As (0.3). <i>Applied Physics Letters</i> , <b>1989</b> , 54, 721-723	3.4	17
116	Modulation-doped In <sub>0.3</sub> Ga <sub>0.7</sub> As/In <sub>0.29</sub> Al <sub>0.71</sub> As heterostructures grown on GaAs by step grading. <i>Semiconductor Science and Technology</i> , <b>1992</b> , 7, 601-603	1.8	16
115	High-resolution x-ray diffraction of InAlAs/InP superlattices grown by gas source molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>1991</b> , 58, 1530-1532	3.4	16
114	Space-charge-limited current in nanowires. <i>Journal of Applied Physics</i> , <b>2017</b> , 121, 174301	2.5	15
113	Structural and magnetic properties of NiMnSb/InGaAs/InP(001). <i>Journal of Applied Physics</i> , <b>2005</b> , 97, 073906	2.5	15
112	Lithography-Free Fabrication of Core-Shell GaAs Nanowire Tunnel Diodes. <i>Nano Letters</i> , <b>2015</b> , 15, 5408-5413	11.5	14
111	p-type doping of GaAs nanowires using carbon. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 094323	2.5	14
110	Role of interface microstructure in rectifying metal/semiconductor contacts: Ballistic electron emission observations correlated to microstructure. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1996</b> , 14, 1828		14
109	Au/ZnSe contacts characterized by ballistic electron emission microscopy. <i>Journal of Applied Physics</i> , <b>1996</b> , 79, 1532-1535	2.5	14
108	Large-Area Low-Cost Flexible Plastic Nanohole Arrays for Integrated Bio-Chemical Sensing. <i>IEEE Sensors Journal</i> , <b>2013</b> , 13, 3982-3990	4	13
107	Electrodeposition, characterization and morphological investigations of NiFe/Cu multilayers prepared by pulsed galvanostatic, dual bath technique. <i>Materials Characterization</i> , <b>2011</b> , 62, 204-210	3.9	12
106	Relaxation-induced polarized luminescence from In <sub>x</sub> Ga <sub>1-x</sub> As films grown on GaAs(001). <i>Physical Review B</i> , <b>1995</b> , 51, 5033-5037	3.3	12
105	Optical detection of misfit dislocation-induced deep levels at InGaAs/GaAs heterojunctions. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 3572-3574	3.4	12
104	Residual Stress, Defects, and Electrical Properties of Epitaxial Copper Growth on GaAs. <i>Journal of the Electrochemical Society</i> , <b>2009</b> , 156, D138	3.9	11

103	Controlled axial and radial Te-doping of GaAs nanowires. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 054324	2.5	11
102	Tensile strain relaxation in GaN <sub>x</sub> P <sub>1-x</sub> (x=0.1) grown by chemical beam epitaxy. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1996</b> , 14, 2952		11
101	Ballistic electron and photocurrent transport in Au-molecular layer-GaAs diodes. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 013703	2.5	11
100	Faceting transition in epitaxial growth of dilute GaNAs films on GaAs. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2001</b> , 19, 1417		11
99	Effect of Bi surfactant on atomic ordering of GaAsSb. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 5589-5591	3.4	10
98	The Polycrystalline-Si Contact to GaAs. <i>Journal of the Electrochemical Society</i> , <b>1986</b> , 133, 1176-1179	3.9	10
97	Long-lasting flexible organic solar cells stored and tested entirely in air. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 263305	3.4	9
96	Planar defects and phase transformation in ZnSe nanosaws. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2006</b> , 17, 1065-1070	2.1	9
95	The growth of SiGe on sapphire using rapid thermal chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2001</b> , 222, 20-28	1.6	9
94	Correlation of buffer strain relaxation modes with transport properties of two-dimensional electron gases. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 6849-6854	2.5	9
93	Role of Hydrogen Evolution during Epitaxial Electrodeposition of Fe on GaAs. <i>Journal of the Electrochemical Society</i> , <b>2018</b> , 165, H3076-H3079	3.9	8
92	Growth of h-BN on copper (110) in a LEEM. <i>Surface Science</i> , <b>2018</b> , 669, 133-139	1.8	8
91	Epitaxial Fe <sub>x</sub> Ni <sub>1-x</sub> Thin Film Contacts to GaAs via Electrochemistry. <i>Journal of the Electrochemical Society</i> , <b>2008</b> , 155, H841	3.9	8
90	Effects of capillary forces on copper dielectric interfacial void evolution. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 5201-5203	3.4	8
89	Hole confinement and low-frequency noise in SiGe pFETs on silicon-on-sapphire. <i>IEEE Electron Device Letters</i> , <b>1999</b> , 20, 173-175	4.4	8
88	Comparison of Au contacts to Si, GaAs, In <sub>x</sub> Ga <sub>1-x</sub> P, and ZnSe measured by ballistic electron emission microscopy. <i>Materials Chemistry and Physics</i> , <b>1996</b> , 46, 224-229	4.4	8
87	Si diffusion and segregation in low-temperature grown GaAs. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 286-288	3.4	8
86	Lateral spin injection and detection through electrodeposited Fe/GaAs contacts. <i>Semiconductor Science and Technology</i> , <b>2013</b> , 28, 035003	1.8	7

85	Detecting Antibodies Secreted by Trapped Cells Using Extraordinary Optical Transmission. <i>IEEE Sensors Journal</i> , <b>2011</b> , 11, 2732-2739	4	7
84	Modulation-doped In <sub>0.53</sub> Ga <sub>0.47</sub> As/In <sub>0.52</sub> Al <sub>0.48</sub> As heterostructures grown on GaAs substrates using step-graded In <sub>x</sub> Ga <sub>1-x</sub> As buffers. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1996</b> , 14, 3035		7
83	Strain relaxation by <100> misfit dislocations in dilute nitride In <sub>x</sub> Ga <sub>1-x</sub> As <sub>1-y</sub> N <sub>y</sub> /GaAs quantum wells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2005</b> , 202, 2849-2857	1.6	7
82	Room-temperature electrosynthesis of carbonaceous fibers. <i>Advanced Materials</i> , <b>1995</b> , 7, 398-401	24	7
81	Aligned cuboid iron nanoparticles by epitaxial electrodeposition. <i>Nanoscale</i> , <b>2017</b> , 9, 5315-5322	7.7	6
80	Electrical properties of lightly Ga-doped ZnO nanowires. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 125010	1.8	6
79	Interfacial reactions at Fe/topological insulator spin contacts. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2017</b> , 35, 04F105	1.3	6
78	Plasmonic sensors based on nano-holes: technology and integration <b>2008</b> ,		6
77	AuAg and AuPd molecular contacts to GaAs. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2008</b> , 26, 1597		6
76	Recycling gold nanohole arrays. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2014</b> , 32, 031403	2.9	5
75	Improved chemical and electrical stability of gold silicon contacts via epitaxial electrodeposition. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 063708	2.5	5
74	Atomic ordering in GaAsSb (0 0 1) grown by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 4391-4397	1.6	5
73	Transparent conducting indium bismuth oxide. <i>Thin Solid Films</i> , <b>2007</b> , 515, 3760-3765	2.2	5
72	Structural and electrical characteristics of microcrystalline silicon prepared by hot-wire chemical vapor deposition using a graphite filament. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2007</b> , 25, 464-467	2.9	5
71	Interfacial scattering of hot electrons in ultrathin Au/Co films. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2000</b> , 18, 2047		5
70	. <i>Journal of Medical and Biological Engineering</i> , <b>2011</b> , 31, 121	2.2	5
69	Evolution of interface voids under current and temperature stress in integrated circuit metallization. <i>Metals and Materials International</i> , <b>2004</b> , 10, 411-415	2.4	4
68	X-Ray Diffuse Scattering from Misfit Dislocation at Buried Interface. <i>Materials Research Society Symposia Proceedings</i> , <b>2001</b> , 673, 1		4



67	Anisotropic Surface Roughness in Strain Relaxed $\text{In}_{0.40}\text{Ga}_{0.60}\text{As}$ on GaAs with a Step-Graded $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}$ Buffer Layer. <i>Materials Research Society Symposia Proceedings</i> , <b>1993</b> , 312, 107		4
66	The Diffusion of Phosphorus and Indium into Gallium Arsenide from Polycrystalline-Silicon. <i>Materials Research Society Symposia Proceedings</i> , <b>1986</b> , 77, 785		4
65	Cw laser crystallization of glow discharge a-Si:H on glass substrates. <i>Journal of Electronic Materials</i> , <b>1982</b> , 11, 303-320	1.9	4
64	Three-Dimensional Imaging of Beam-Induced Biasing of InP/GaInP Tunnel Diodes. <i>Nano Letters</i> , <b>2019</b> , 19, 3490-3497	11.5	3
63	Measuring Surface Energies of GaAs (100) and Si (100) by Three Liquid Contact Angle Analysis (3LCAA) for Heterogeneous Nano-Bonding <sup>TM</sup> . <i>MRS Advances</i> , <b>2018</b> , 3, 3403-3411	0.7	3
62	Regrowth mechanism for oxide isolation of GaAs nanowires. <i>Nanotechnology</i> , <b>2017</b> , 28, 385302	3.4	3
61	<b>2010</b> ,		3
60	Effect of annealing on the structural and optical properties of heavily carbon-doped ZnO. <i>Semiconductor Science and Technology</i> , <b>2010</b> , 25, 045023	1.8	3
59	Microstructure of ordered nanodomains induced by Bi surfactant in OMVPE-grown GaAsSb. <i>Journal of Crystal Growth</i> , <b>2006</b> , 287, 541-544	1.6	3
58	Dislocation-Induced deep level states in $\text{In}_{0.08}\text{Ga}_{0.92}\text{As}/\text{GaAs}$ heterostructures. <i>Journal of Electronic Materials</i> , <b>1994</b> , 23, 929-933	1.9	3
57	Control of surface morphology and strain relaxation in InGaAs grown on GaAs using a step-graded buffer <b>1994</b> , 2140, 179		3
56	Beam Investigation of Oxide and Sulfide Passivated GaAs. <i>Materials Research Society Symposia Proceedings</i> , <b>1992</b> , 281, 653		3
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